

SCDS314B-FEBRUARY 2011-REVISED MAY 2013

# 12-Channel, 1:2 MUX/DEMUX Switch for DDR3 Applications

Check for Samples: TS3DDR3812

## FEATURES

- Compatible with DDR3 SDRAM Standard (JESD79-3D)
- Wide Bandwidth of 1.675 GHz
- Low Propagation Delay (t<sub>pd</sub> = 40 ps Typ)
- Low Bit-to-Bit Skew (t<sub>sk(o)</sub> = 6 ps Typ)
- Low and Flat ON-State Resistance (r<sub>ON</sub> = 8 Ω Typ)
- Low Input/Output Capacitance (C<sub>ON</sub> = 5.6 pF Typ)
- Low Crosstalk (X<sub>TALK</sub> = -43 dB, Typ at 250 MHz)
- V<sub>CC</sub> Operating Range from 3 V to 3.6 V
- Rail-to-Rail Switching on Data I/O Ports (0 to V<sub>CC</sub>)
- Separate Switch Control Logic for Upper and Lower 6-Channels
- Dedicated Enable Logic Supports Hi-Z Mode
- I<sub>OFF</sub> Protection Prevents Current Leakage in Powered Down State (V<sub>CC</sub> = 0 V)
- ESD Performance Tested Per JESD22
  - 2000 V Human Body Model (A114B, Class II)
  - 1000 V Charged Device Model (C101)
- 42-pin RUA Package (9 × 3.5 mm, 0.5 mm Pitch)

## APPLICATIONS

- DDR3 Signal Switching
- DIMM Modules
- Notebook/Desktop PCs
- Servers



### DESCRIPTION

The TS3DDR3812 is a 12-channel, 1:2 multiplexer/demultiplexer switch designed for DDR3 applications. It operates from a 3 to 3.6 V supply and offers low and flat ON-state resistance as well as low I/O capacitance which allow it to achieve a typical bandwidth of 1.675 GHz.

Channels  $A_0$  through  $A_{11}$  are divided into two banks of six bits and are independently controlled via two digital inputs called SEL1 and SEL2. These select inputs control the switch position of each 6-bit DDR3 source and allow them to be routed to one of two end-points. Alternatively, the switch can be used to connect a single endpoint to one of two 6-bit DDR3 sources. For switching 12-bit DDR3 sources, simply connect SEL1 and SEL2 together externally and control all 12 channels with a single GPIO input. An EN input allows the entire chip to be placed into a high-impedance (Hi-Z) state while not in use.

These characteristics make the TS3DDR3812 an excellent choice for use in memory, analog/digital video, LAN, and other high-speed signal switching applications.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

## TS3DDR3812

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **ORDERING INFORMATION**

For package and ordering information, see the Package Option Addendum at the end of this document.



#### Figure 2. LOGIC DIAGRAM

#### FUNCTION TABLE

EN	SEL1	SEL2	FUNCTION
L	х	х	$A_0$ to $A_{11}$ , $B_0$ to $B_{11}$ , and $C_0$ to $C_{11}$ are Hi-Z
Н	L	L	$A_0$ to $A_5 = B_0$ to $B_5$ and $A_6$ to $A_{11} = B_6$ to $B_{11}$
Н	L	Н	$A_0$ to $A_5 = B_0$ to $B_5$ and $A_6$ to $A_{11} = C_6$ to $C_{11}$
Н	Н	L	$A_0$ to $A_5 = C_0$ to $C_5$ and $A_6$ to $A_{11} = B_6$ to $B_{11}$
Н	Н	Н	$A_0$ to $A_5 = C_0$ to $C_5$ and $A_6$ to $A_{11} = C_6$ to $C_{11}$

#### **TERMINAL FUNCTIONS**

PIN	DESCRIPTION			
NAME	NUMBER	DESCRIPTION		
V <sub>CC</sub>	1,17, 30	Supply Voltage		
GND	ThermalPad	Ground		



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#### **TERMINAL FUNCTIONS (continued)**

PIN	DESCRIPTION			
NAME	NUMBER	DESCRIPTION		
EN	8	Enable Input		
SEL1	9	Select Input		
SEL2	10	Select Input		
A <sub>0</sub> , A <sub>1</sub> , A <sub>2</sub> , A <sub>3</sub> , A <sub>4</sub> , A <sub>5</sub> , A <sub>6</sub> , A <sub>7</sub> , A <sub>8</sub> , A <sub>9</sub> , A <sub>10</sub> , A <sub>11</sub>	2, 3, 4, 5, 6, 7, 11, 12, 13, 14, 15, 16	Data I/Os		
B <sub>0</sub> , B <sub>1</sub> , B <sub>2</sub> , B <sub>3</sub> , B <sub>4</sub> , B <sub>5</sub> , B <sub>6</sub> , B <sub>7</sub> , B <sub>8</sub> , B <sub>9</sub> , B <sub>10</sub> , B <sub>11</sub>	41, 39, 38, 36, 34, 32, 29, 27, 25, 23, 21, 19	Data I/Os		
$C_0, C_1, C_2, C_3, C_4, C_5, C_6, C_7, C_8, C_9, C_{10}, C_{11}$	42, 40, 37, 35, 33, 31, 28, 26, 24, 22, 20, 18	Data I/Os		

### **ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>**

over operating free-air temperature range (unless otherwise noted)

				MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range			-0.5	4.6	V
V <sub>I/O</sub>	Analog voltage range <sup>(2)(3)(4)</sup>	A, B, C		-0.5	7	V
V <sub>IN</sub>	Digital input voltage range <sup>(2)(3)</sup>	SEL1, SEL2		-0.5	7	V
I <sub>I/OK</sub>	Analog port diode current	V <sub>I/O</sub> < 0			-50	mA
I <sub>IK</sub>	Digital input clamp current	V <sub>IN</sub> < 0			-50	mA
I <sub>I/O</sub>	On-state switch current <sup>(5)</sup>	A, B, C		-128	128	mA
I <sub>DD</sub> , I <sub>GND</sub>	Continuous current through $V_{\text{DD}}$ or	GND		-100	100	mA
$\theta_{JA}$	Package thermal impedance <sup>(6)</sup>	RUA package			31.8	°C/W
T <sub>stg</sub>	Storage temperature range				150	°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings (1) only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltages are with respect to ground, unless otherwise specified. (2)

The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.  $V_I$  and  $V_O$  are used to denote specific conditions for  $V_{I/O}$ . (3)

(4)

 $I_{\underline{l}}$  and  $I_{O}$  are used to denote specific conditions for  $I_{\underline{l}/O}$ (5)

(6) The package thermal impedance is calculated in accordance with JESD 51-7. SCDS314B-FEBRUARY 2011-REVISED MAY 2013

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STRUMENTS

EXAS

### **RECOMMENDED OPERATING CONDITIONS<sup>(1)</sup>**

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage		3	3.6	V
$V_{\text{IH}}$	High-level control input voltage	SEL1, SEL2	2	5.5	V
$V_{\text{IL}}$	Low-level control input voltage	SEL1, SEL2	0	0.8	V
V <sub>IN</sub>	Input voltage	SEL1, SEL2	0	5.5	V
V <sub>I/O</sub>	Input/Output voltage	0	$V_{CC}$	V	
T <sub>A</sub>	Operating free-air temperature	-40	85	°C	

(1) All unused control inputs of the device must be held at V<sub>DD</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004

## **ELECTRICAL CHARACTERISTICS**

over recommended operating free-air temperature range,  $V_{CC}$  = 3.3 V ± 0.3 V (unless otherwise noted)

	PARAMETER		TEST CONDITIONS <sup>(1)</sup>	MIN	TYP <sup>(2)</sup>	MAX	UNIT
V <sub>IK</sub>	Digital input clamp voltage	SEL1, SEL2	$V_{CC} = 3.6 \text{ V}, \text{ I}_{IN} = -18 \text{ mA}$	-1.2	-0.8		V
R <sub>ON</sub>	ON-state resistance	A, B, C	$\label{eq:VCC} \begin{array}{l} V_{CC} = 3 \ V, \ 1.5 \ V \leq V_{I/O} \leq V_{CC}, \\ I_{I/O} = -40 \ \text{mA} \end{array}$		8	12	Ω
R <sub>ON(flat)</sub> <sup>(3)</sup>	ON-state resistance flatness	A, B, C	$V_{CC}$ = 3 V, $V_{I/O}$ = 1.5 V and $V_{CC},$ $I_{I/O}$ = –40 mA		1.5		Ω
$\Delta R_{ON}^{(4)}$	On-state resistance match between channels	A, B, C	$V_{CC} = 3 \text{ V}, 1.5 \text{ V} \le V_{I/O} \le V_{CC},$ $I_{I/O} = -40 \text{ mA}$		0.4	1	Ω
IIH	Digital input high leakage current	SEL1, SEL2	$V_{CC} = 3.6 \text{ V}$ , $V_{IN} = V_{DD}$			±1	μA
I <sub>IL</sub>	Digital input low leakage current	SEL1, SEL2	$V_{CC}$ = 3.6 V, $V_{IN}$ = GND			±1	μΑ
I <sub>OFF</sub>	Leakage under power off conditions	All outputs	$V_{CC}$ = 0 V, $V_{I/O}$ = 0 to 3.6 V, $V_{IN}$ = 0 to 5.5 V			±1	μΑ
C <sub>IN</sub>	Digital input capacitance	SEL1, SEL2	f = 1 MHz, V <sub>IN</sub> = 0 V		2.6	3.2	pF
C <sub>OFF</sub>	Switch OFF capacitance	A, B, C	f = 1 MHz, V <sub>I/O</sub> = 0 V, Output is open, Switch is OFF		2		pF
C <sub>ON</sub>	Switch ON capacitance	A, B, C	f = 1 MHz, $V_{I/O}$ = 0 V, Output is open, Switch is ON		5.6		pF
I <sub>CC</sub>	V <sub>CC</sub> supply current		$V_{CC}$ = 3.6 V, $I_{I/O}$ = 0, $V_{IN}$ = $V_{DD}$ or GND		300	400	μA

 $\begin{array}{ll} (1) & V_{I}, \, V_{O}, \, I_{I}, \, \text{and} \, I_{O} \, \text{refer to } \, I/O \, \text{pins}, \, V_{IN} \, \text{refers to the control inputs} \\ (2) & \text{All typical values are at} \, V_{CC} = 3.3 V \, (\text{unless otherwise noted}), \, T_{A} = 25^{\circ}\text{C} \\ (3) & R_{ON(FLAT)} \, \text{is the difference of } R_{ON} \, \text{in a given channel at specified voltages.} \\ (4) & \Delta R_{ON} \, \text{is the difference of } R_{ON} \, \text{from center port} \, (A_{5}, \, A_{6}) \, \text{to any other ports.} \end{array}$ 

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#### SWITCHING CHARACTERISTICS

Over recommended operation free-air temperature range,  $V_{CC}$  = 3.3 V ± 0.3 V,  $R_L$  = 200  $\Omega$ ,  $C_L$  = 4 pF (unless otherwise noted) (see Figure 7 and Figure 9)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN TYP <sup>(*</sup>	) MAX	UNIT	
t <sub>pd</sub> <sup>(2)</sup>	A or B,C	B,C or A	4	)	ps	
t <sub>PZH</sub> , t <sub>PZL</sub>	SEL1	A <sub>0-5</sub> or B <sub>0-5</sub> , C <sub>0-5</sub>	2	7	ns	
	SEL2	A <sub>6-11</sub> or B <sub>6-11</sub> , C <sub>6-11</sub>	2	7	ns	
t <sub>PHZ</sub> , t <sub>PLZ</sub>	SEL1	A <sub>0-5</sub> or B <sub>0-5</sub> , C <sub>0-5</sub>	2	5	ns	
	SEL2	A <sub>6-11</sub> or B <sub>6-11</sub> , C <sub>6-11</sub>	2	5	ns	
t <sub>sk(0)</sub> <sup>(3)</sup>	A or B,C	B, C or A		5 30	ps	
$t_{sk(p)}^{(4)}$	A or B, C	B, C or A	1	5 30	ps	

(1)

All typical values are at  $V_{CC}$  = 3.3V (unless otherwise noted),  $T_A$  = 25°C. The propagation delay is the calculated RC time constant of the typical ON-State resistance of the switch and the specified load (2) capacitance when driven by an ideal voltage source (zero output impedance).

Output skew between center port (A5, A6) and any other channel. (3)

(4) Skew between opposite transitions of the same output |t<sub>PHL</sub> - t<sub>PLH</sub>|

### **DYNAMIC CHARACTERISTICS**

over recommended operating free-air temperature range,  $V_{CC}$  = 3.3 V ± 0.3 V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TYP <sup>(1)</sup>	UNIT
X <sub>TALK</sub>	$R_L = 50 \Omega$ , f = 250 MHz (see Figure 11)	-43	dB
O <sub>IRR</sub>	$R_L = 50 \Omega$ , f = 250 MHz (see Figure 12)	-42	dB
BW	$R_L = 50 \Omega$ , Switch ON (see Figure 10)	1.675	GHz

(1) All Typical Values are at  $V_{CC}$  = 3.3 V (unless otherwise noted),  $T_A$  = 25°C.

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### **OPERATING CHARACTERISTICS**









#### PARAMETER MEASUREMENT INFORMATION



TEST	V <sub>DD</sub>	V <sub>DD</sub> S1 R <sub>L</sub>		V <sub>in</sub>	CL	$V_{\Delta}$	
t <sub>PLZ</sub> /t <sub>PZL</sub>	3.3 V ± 0.3 V	2 × V <sub>DD</sub>	200 Ω	GND	4 pF	0.3 V	
t <sub>PHZ</sub> /t <sub>PZH</sub>	3.3 V ± 0.3 V	GND	200 Ω	V <sub>DD</sub>	4 pF	0.3 V	



ENABLE AND DISABLE TIMES

- NOTES: A. C<sub>L</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$ 10 MHz, Z<sub>0</sub> = 50  $\Omega$ , t<sub>r</sub>  $\leq$  2.5 ns. t<sub>f</sub>  $\leq$  2.5 ns.
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E.  $t_{\text{PLZ}} \, \text{and} \, t_{\text{PHZ}} \, \text{are the same as} \, t_{\text{dis}}.$
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .

#### Figure 7. Test Circuit and Voltage Waveforms

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#### PARAMETER MEASUREMENT INFORMATION (continued)



TEST	V <sub>CC</sub>	S1	RL	V <sub>in</sub>	CL
t <sub>sk(o)</sub>	3.3 V ± 0.3 V	Open	200 Ω	$V_{CC}$ or GND	4 pF
t <sub>sk(p)</sub>	3.3 V ± 0.3V	Open	200 Ω	V <sub>CC</sub> or GND	4 pF



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq 10$  MHz,  $Z_0 = 50 \Omega$ ,  $t_r \leq 2.5$  ns.  $t_f \leq 2.5$  ns.
- D. The outputs are measured one at a time, with one transition per measurement.

Figure 9. Test Circuit andf Voltage Waveforms



#### PARAMETER MEASUREMENT INFORMATION (continued)



#### Figure 10. Test Circuit for Frequency Response (BW)

Frequency response is measured at the output of the ON channel. For example, when  $V_{SEL} = 0$  and  $A_0$  is the input, the output is measured at B0. All unused analog I/O ports are left open.

### HP8753ES Setup

Average = 4 RBW = 3 kHz  $V_{BIAS}$  = 0.35 V ST = 2 s P1 = 0 dBM

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### PARAMETER MEASUREMENT INFORMATION (continued)



A. C<sub>1</sub> includes probe and jig capacitance.

B. A 50 W termination resistor is needed to match the loading of the network analyzer.

Figure 11. Test Circuit for Crosstalk (X<sub>TALK</sub>)

Crosstalk is measured at the output of the nonadjacent ON channel. For example, when  $V_{SEL} = 0$  and  $A_1$  is the input, the output is measured at  $A_3$ . All unused analog input (A) ports are connected to GND, and output (B) ports are left open.

#### HP8753ES Setup

Average = 4 RBW = 3 kHz  $V_{BIAS}$  = 0.35 V ST = 2 s P1 = 0 dBM





PARAMETER MEASUREMENT INFORMATION (continued)

B. A 50 W termination resistor is needed to match the loading of the network analyzer.

#### Figure 12. Test Circuit for OFF Isolation (O<sub>IRR</sub>)

OFF isolation is measured at the output of the OFF channel. For example, when  $V_{SEL} = GND$  and  $A_1$  is the input, the output is measured at 1B<sub>2</sub>. All unused analog input (A) ports are connected to ground, and output (B) ports are left open.

#### HP8753ES Setup

Average = 4 RBW = 3 kHz  $V_{BIAS}$  = 0.35 V ST = 2 s P1 = 0 dBM

A.  $C_{\scriptscriptstyle L}$  includes probe and jig capacitance.

### **REVISION HISTORY**

Changes from Revision A (March 2012) to Revision B

• Changed Low B Low Bit-to-Bit Skew in the FEATURES list from ( $t_{sk(o)} = 6$  ps Max) to ( $t_{sk(o)} = 6$  ps Typ) ..... 1

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10-Dec-2020

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS3DDR3812RUAR	ACTIVE	WQFN	RUA	42	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	SL812	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(<sup>6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3DDR3812RUAR	WQFN	RUA	42	3000	330.0	16.4	3.8	9.3	1.0	8.0	16.0	Q1

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## PACKAGE MATERIALS INFORMATION

3-Aug-2017



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3DDR3812RUAR	WQFN	RUA	42	3000	358.0	335.0	35.0

## **RUA 42**

9 x 3.5, 0.5 mm pitch

# **GENERIC PACKAGE VIEW**

## WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





# **RUA0042A**



# **PACKAGE OUTLINE**

## WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



# **RUA0042A**

# **EXAMPLE BOARD LAYOUT**

### WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

 This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



# **RUA0042A**

# **EXAMPLE STENCIL DESIGN**

## WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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